

IN THE CLAIMS

1 (Currently Amended). A method comprising:
blending a photodefinable polybenzoxazole precursor with ~~a filler~~ zirconia particles having a particle size of less than 100 nanometers.

Claims 2 and 3 (Canceled).

4 (Currently Amended). The method of claim 1 including blending the photodefinable precursor with ~~a filler~~ zirconia particles having a particle size less than 20 nanometers.

5 (Currently Amended). The method of claim 1 including blending the photodefinable precursor with ~~a filler~~ zirconia particles having a particle size of about 13 nanometers.

6 (Currently Amended). The method of claim 1 including curing the precursor after blending with ~~a filler~~ zirconia particles.

7 (Currently Amended). The method of claim 1 including blending the precursor with a filler so that ~~the filler constitutes~~ zirconia particles constitute from about 9 to about 20 percent by weight.

8 (Currently Amended). The method of claim 1 including forming a polymer from said blended precursor and ~~filler~~ zirconia particles.

9 (Currently Amended). A photodefinable polymer for semiconductor applications comprising:
a photodefinable polybenzoxazole precursor; and
~~a filler material~~ zirconia particles having a particle size of less than 100 nanometers.

Claims 10 and 11 (Canceled).

12 (Currently Amended). The polymer of claim 9 wherein said ~~filler material has~~ zirconia particles have a particle size of less than 20 nanometers.

13 (Currently Amended). The polymer of claim 9 wherein said ~~filler material has~~ zirconia particles have a particle size of about 13 nanometers.

14 (Currently Amended). The polymer of claim 9 wherein said ~~filler material~~ comprises zirconia particles comprise from about 9 to about 20 percent by weight.

15 (Currently Amended). A photodefinable polymer for semiconductor applications comprising:

a photodefinable polybenzoxazole precursor; and

~~a filler~~ zirconia particles comprising about 9 to about 20 percent of the system, said ~~filler~~ particles having a particle size of less than 20 nanometers.

Claims 16 and 17 (Canceled).

18 (Currently Amended). The polymer of claim 15 wherein said ~~filler has~~ zirconia particles have a particle size of approximately 13 nanometers.

19 (Currently Amended). A polymer precursor for semiconductor applications comprising:

a photodefinable polybenzoxazole precursor; and

~~a filler material~~ zirconia particles having a particle size of less than 100 nanometers.

Claims 20 and 21 (Canceled).

22 (Currently Amended). The precursor of claim 19 wherein said ~~filler material~~ has zirconia particles have a particle size of less than 20 nanometers.

23 (Currently Amended). The precursor of claim 19 wherein said ~~filler material~~ has zirconia particles have a particle size of about 13 nanometers.

24 (Currently Amended). The precursor of claim 19 wherein said ~~filler material~~ ~~comprises~~ zirconia particles comprise about 9 to about 20 percent by weight.

25 (Currently Amended). An integrated circuit comprising:
a substrate; and
a photodefinable polymer formed on said substrate, said polymer including a photodefinable resin and a ~~filler material~~ zirconia particles having a particle size of less than 100 nanometers.

Claims 26 and 27 (Canceled).

28 (Currently Amended). The circuit of claim 25 wherein said ~~filler material~~ has zirconia particles have a particle size of less than 20 nanometers.

29 (Currently Amended). The circuit of claim 25 wherein said ~~filler material~~ has zirconia particles have a particle size of about 13 nanometers.

30 (Currently Amended). The circuit of claim 25 wherein said ~~filler material~~ ~~comprises~~ zirconia particles comprise from about 9 to about 20 percent by weight.